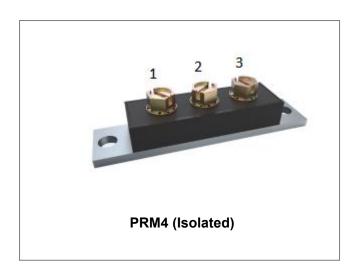






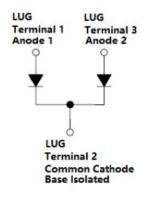
303CMQ600 ULTRAFAST RECTIFIER



Features

- 175 °C T_J operation
- · Center tap module
- . High purity, high temperature epoxy encapsulation for
- enhanced mechanical strength and moisture resistance
- Low forward voltage drop
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- Base plate: Nickel plated; Terminals: Nickel plated
- The terminal hardware is supplied with the module.
- The mounting hardware is not supplied. Recommended is the use of 1/4-20 or M6 screws with spring washer.
- This is a Pb Free Device
- All SMC parts are traceable to the wafer lot
- · Additional testing can be offered upon request

Circuit Diagram



Applications

- · High current switching power supply
- Plating power supply
- Free-Wheeling diodes
- Reverse battery protection
- Converters
- UPS System
- Welding

Maximum Ratings(limiting values, at 25 °C unless otherwise specified)

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _R	-	600	V
Average Rectified Forward Current	I _{F (AV)}	50% duty cycle @T _C =117°C, rectangular wave form	150(Per leg) 300(Per device)	Α
Peak One Cycle Non-Repetitive Surge Current	I _{FSM}	8.3 ms, half Sine pulse	3000	А
Non-Repetitive Avalanche Energy(per leg)	Eas	TJ=25°C,IAS=1A,L=30mH	15	mJ
Repetitive avalanche current (per leg)	lar	Current decaying linearly to zero in 1µsec frequency limited by TJ max.VA=1.5X VR typical	1	А

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Electrical Characteristics:

Characteristics	Symbol	Condition	Тур.	Max.	Units
Forward Voltage Drop*	V _{F1}	@ 150A, Pulse, T _J = 25 °C @ 300 A, Pulse, T _J = 25 °C	1.07 1.20	1.40 1.68	V
	V _{F2}	@ 150A, Pulse, T _J = 125 °C @ 300 A, Pulse, T _J = 125 °C	0.96 1.08	1.20 1.38	V
Reverse Current *	I _{R1}	@V _R = rated V _R T _J = 25 °C	0.0003	0.1	mA
	I _{R2}	@V _R = rated V _R T _J = 125 °C	0.04	20	mA
Junction Capacitance	Ст	$@V_R = 5V, T_C = 25 ^{\circ}C$ $f_{SIG} = 1MHz$	730	4150	pF

 $^{^*}$ Pulse width < 300 μ s, duty cycle < 2%

Thermal-Mechanical Specifications:

Characteristics	Symbol	Condition	Specification		Units
Junction Temperature	TJ	-	-55 to +175		°C
Storage Temperature	T _{stg}	-	-55 to +175		°C
Typical Thermal Resistance Junction to Case (per leg)	R ₀ JC	DC operation	0.30		°C/W
Typical Thermal Resistance Junction to Case (per package)	R ₀ JC	DC operation	0.15		°C/W
Typical Thermal Resistance, Case to Heat Sink	R _{θCS}	Mounting surface, smooth and greased	0.05		°C/W
Approximate Weight	wt	-	110		g
Mounting Torque	Тм	-	Mounting Torque	3.84(min) 4.80(max)	Nm
Mounting Torque	Тм	-	Terminal Torque	2.35(min) 3.43(max)	INIII
Case Style	PRM4 Isolated				

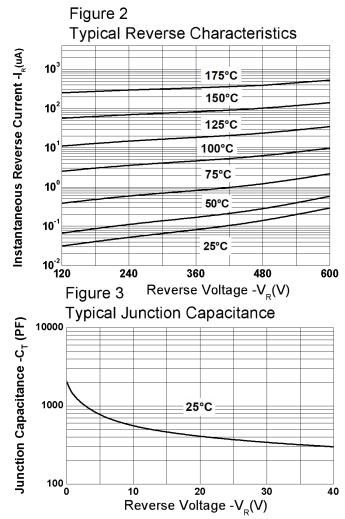
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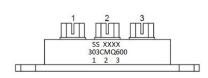
Ratings and Characteristics Curves



Ordering Information

Device	Package	Shipping	
303CMQ600	PRM4 (Isolated) (Pb-Free)	9pcs/ box	

Marking Diagram



Where XXXX is YYWW

1st row SS YYWW
2nd row 303CMQ600
SS = SS
YY = Year
WW = Week

Cautions: Molding resin Epoxy resin UL:94V-0

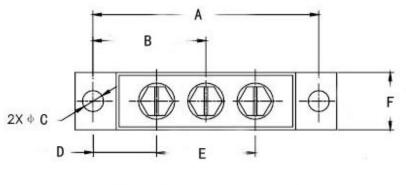
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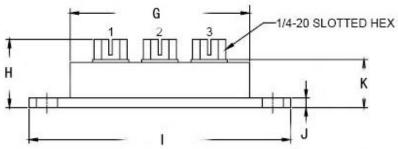






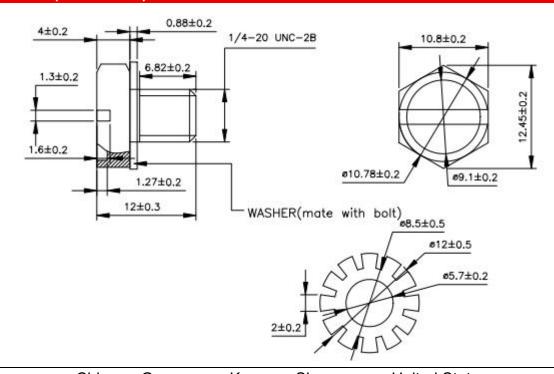
Mechanical Dimensions PRM4 Isolated(Millimeters/Inches)





SYMBOL	Millimeters		Inches		
	Min.	Max.	Min.	Max.	
А	78.74	81.28	3.100	3.200	
В	37.47	42.55	1.475	1.675	
С	6.89	7.69	0.271	0.303	
D	19.51	24.59	0.768	0.968	
Е	33.02	38.10	1.300	1.500	
F	17.78	20.32	0.700	0.800	
G	60.96	64.77	2.400	2.550	
Н	17.56	23.55	0.691	0.927	
I	90.17	92.71	3.550	3.650	
J	3.02	3.68	0.119	0.145	
K	15.75	17.50	0.620	0.689	

1/4-20 screws (Millimeters)



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